

# HiPerFET™

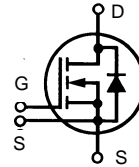
## Power MOSFETs

### Single Die MOSFET

IXFN 80N50  
IXFN 75N50

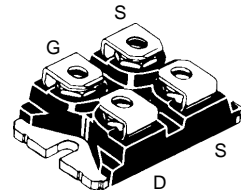
$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
500 V	80 A	50 mΩ
500 V	75 A	55 mΩ

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low  $t_{rr}$



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$ , Chip capability	75N50: 75 80N50: 80	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	75N50: 300 80N50: 320	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	80	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	64	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	6	J
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	700	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS $t = 1\text{ min}$ $I_{ISOL} \leq 1\text{ mA}$ $t = 1\text{ s}$	2500 3000	V~ V~
$M_d$	Mounting torque Terminal connection torque	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B (IXFN)  
E153432



G = Gate  
S = Source  
D = Drain

Either Source terminal of miniBLOC can be used as Main or Kelvin Source

#### Features

- International standard packages
- miniBLOC, with Aluminium nitride isolation
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

#### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

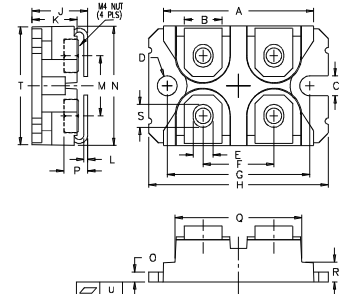
#### Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 3\text{ mA}$	500		V
$V_{GH(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8\text{ mA}$	2		4 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 200\text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0\text{ V}$			$T_J = 25^\circ\text{C}$ : 100 $\mu\text{A}$ $T_J = 125^\circ\text{C}$ : 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5\ I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			80N50: 50 mΩ 75N50: 55 mΩ

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 15\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	50	70	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9890	pF
$C_{oss}$			1750	pF
$C_{rss}$			460	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		61	ns
$t_r$			70	ns
$t_{d(off)}$			102	ns
$t_f$			27	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		380	nC
$Q_{gs}$			80	nC
$Q_{gd}$			173	nC
$R_{thJC}$			0.18	K/W
$R_{thCK}$			0.05	K/W

### miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$	75N50 80N50		75 A 80 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	75N50 80N50		300 A 320 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.3 V
$t_{rr}$	$I_F = 30\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
$Q_{RM}$		1.2		$\mu\text{C}$
$I_{RM}$		8		A

IXYS reserves the right to change limits, test conditions, and dimensions.

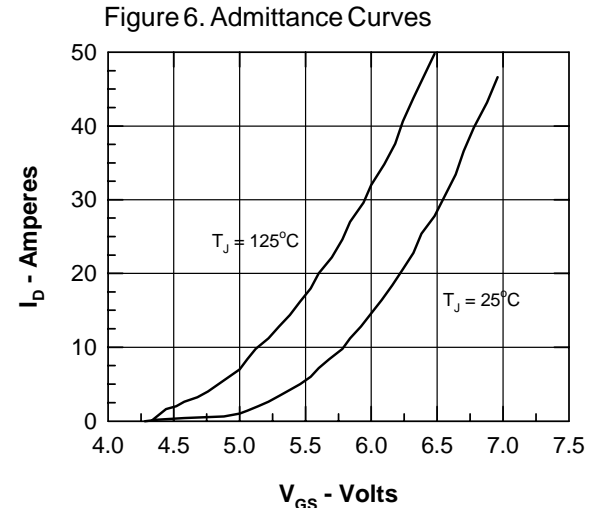
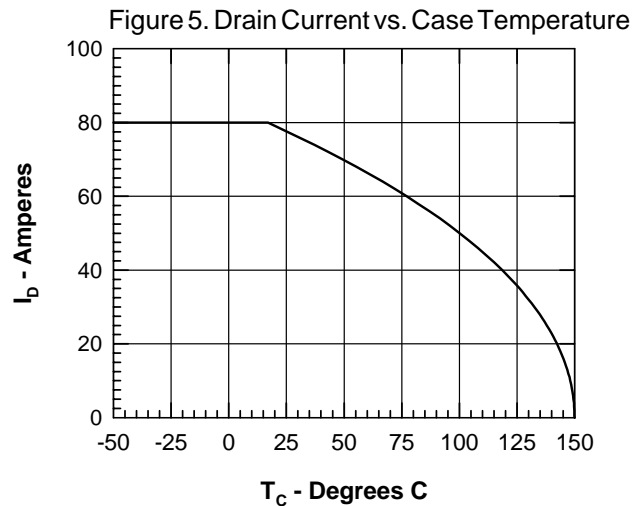
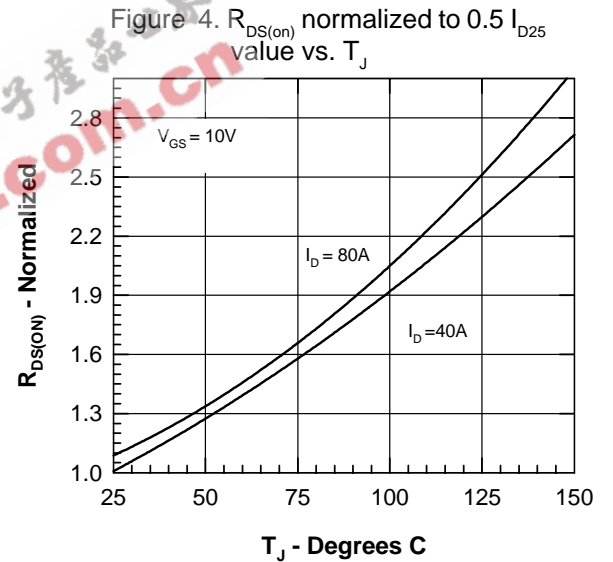
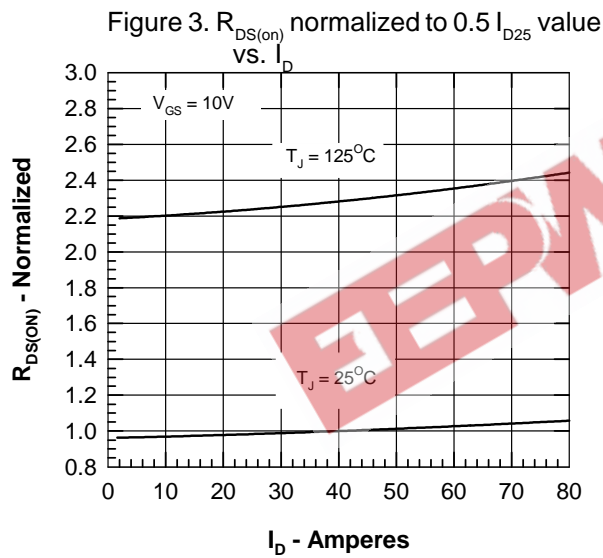
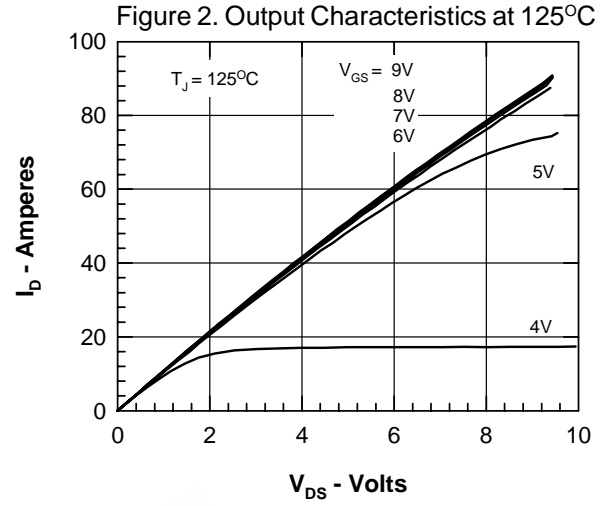
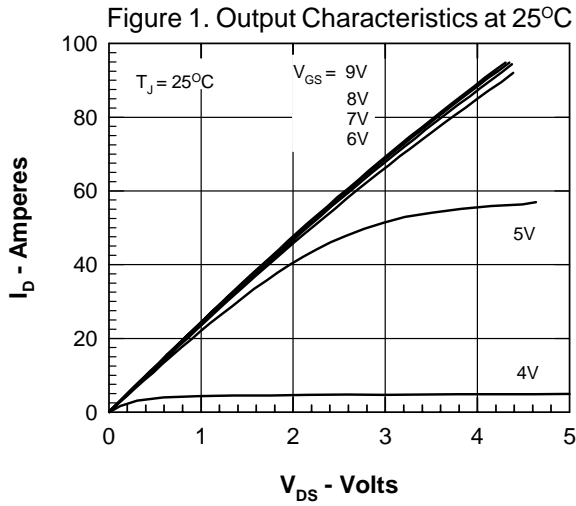


Figure 7. Gate Charge

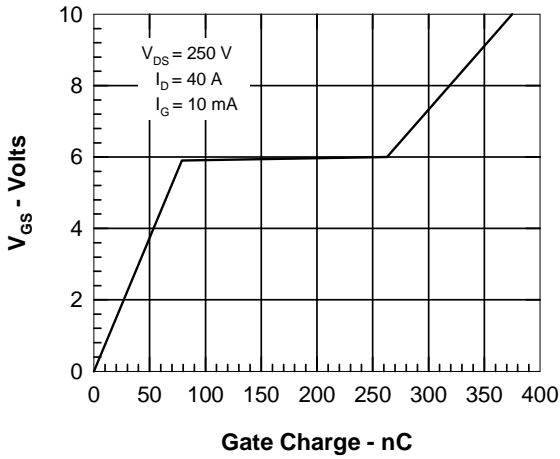


Figure 8. Capacitance Curves

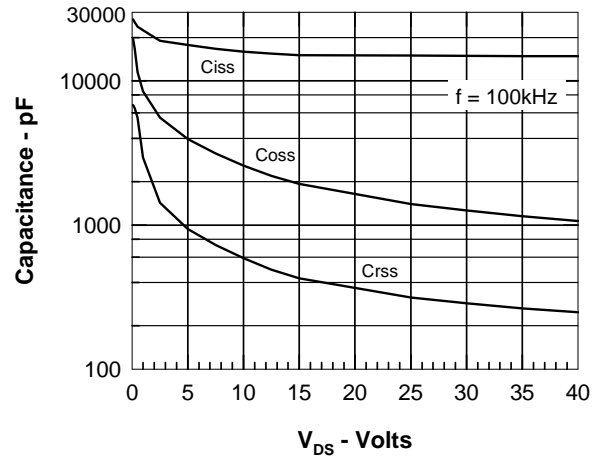


Figure 9. Forward Voltage Drop of the Intrinsic Diode

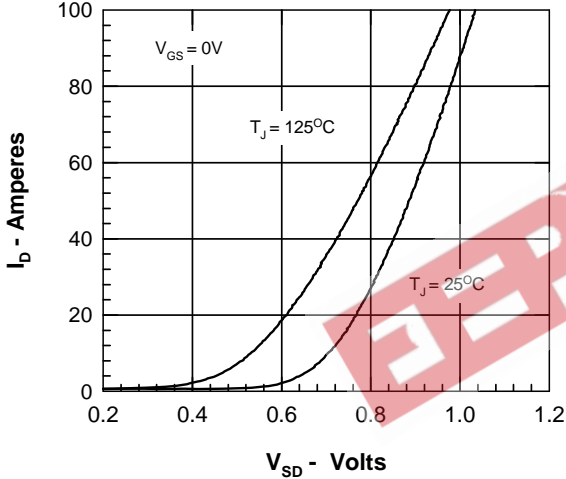


Figure 10. Transient Thermal Resistance

